DGTD65T60S2PT

650V FIELD STOP IGBT IN TO-247

Description

The DGTD65T60S2PT is produced using advanced Field Stop Trench IGBT 2nd Generation Technology, which not only gives high-switching efficiency, but is also extremely rugged and excellent quality for applications where low conduction losses are essential.

Features

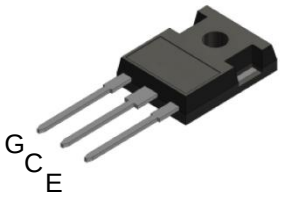
- High Speed Switching & Low Power Loss
- $V_{CE(sat)}$ = 1.85V @ I_C = 60A
- High Input Impedance
- t_{rr} = 110ns (typ) @ di_F/dt = 500A/µs
- E_{off} = 0.53mJ @ T_C=25˚C
- Maximum Junction Temperature 175˚C
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Applications

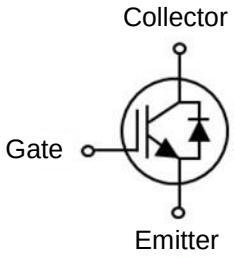
- UPS
- Welder
- Solar Inverter
- IH Cooker

Mechanical Data

- Case: TO-247 (Type MC)
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Terminals: Finish – Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 e3
- Weight: 5.6 grams (Approximate)



TO-247



Device Symbol

Ordering Information (Note 4)

Product	Marking	Quantity
DGTD65T60S2PT	DGTD65T60S2	450 per Box in Tubes (Note 5)

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.
5. 30 Devices per Tube.

Marking Information

Ↄ¦¦ = Manufacturer's Marking
DGTD65T60S2 = Product Type Marking Code
YY = Year (ex: 18 = 2018)
LLLLL = Lot Code
WW = Week (01 to 53)

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Collector-Emitter Voltage		V_{CE}	650	V
DC Collector Current, limited by T_{vjmax}	T_C = 25°C	I_C	100	A
	T_C = 100°C		60	A
Pulsed Collector Current, t_p limited by T_{vjmax}		I_{Cpuls}	180	A
Turn Off Safe Operating Area $V_{CE} \leq$ 650V, T_{vj} = 175°C		-	180	A
Diode Forward Current limited by T_{vjmax}	T_C = 25°C	I_F	60	A
	T_C = 100°C		30	A
Diode Pulsed Current, t_p limited by T_{vjmax}		I_{Fpuls}	200	A
Gate-Emitter Voltage		V_{GE}	±20	V
Short Circuit Withstand Time $V_{CC} \leq$ 400V, R_G=7Ω, V_{GE} = 15V, T_{vj} = 150°C Allowed Number of Short Circuits < 1000 Time Between Short Circuits ≥ 1.0s		tsc	5	µs

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 6)	T_C = 25°C	P_D	428	W
	T_C = 100°C		214	
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	40	°C/W
Thermal Resistance, Junction to Case for IBGT (Note 6)		$R_{\theta JC}$	0.35	
Thermal Resistance, Junction to Case for Diode (Note 6)		$R_{\theta JC}$	1.20	
Operating Temperature		T_{vj}	-40 to +175	°C
Storage Temperature Range		T_{STG}	-55 to +150	

Note: 6. When mounted on a standard JEDEC 2-layer FR-4 board.

Electrical Characteristics (@T_{vj} = +25°C, unless otherwise specified.)

Parameter		Symbol	Min	Typ	Max	Unit	Condition
STATIC CHARACTERISTICS							
Collector-Emitter Breakdown Voltage		BV_{CES}	650	–	–	V	I_C = 2mA, V_{GE} = 0V
Collector-Emitter Saturation Voltage	T_{vj} = 25°C	$V_{CE(sat)}$	–	1.85	2.40	V	I_C = 60A, V_{GE} = 15V
	T_{vj} = 175°C		–	2.60	–		
Diode Forward Voltage	T_{vj} = 25°C	V_F	–	1.45	2.00	V	V_{GE} = 0V, I_F = 25A
	T_{vj} = 175°C		–	1.35	–		
Gate-Emitter Threshold Voltage		$V_{GE(th)}$	4.0	5.0	6.0	V	V_{CE} = V_{GE}, I_C = 0.5mA
Zero Gate Voltage Collector Current		I_{CES}	–	–	40	μA	V_{CE} = 650V, V_{GE} = 0V
Gate-Emitter Leakage Current		I_{GES}	–	–	±100	nA	V_{GE} = 20V, V_{CE} = 0V
DYNAMIC CHARACTERISTICS							
Total Gate Charge		Q_g	–	95	–	nC	V_{CE} = 520V, I_C = 60A, V_{GE} = 15V
Gate-Emitter Charge		Q_{ge}	–	19	–		
Gate-Collector Charge		Q_{gc}	–	47	–		
Input Capacitance		C_{ies}	–	2,327	–	pF	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz
Reverse Transfer Capacitance		C_{res}	–	55	–		
Output Capacitance		C_{oes}	–	270	–		
Internal Emitter Inductance Measured 5mm (0.197") From Case		L_E	–	13	–	nH	–
SWITCHING CHARACTERISTICS							
Turn-on Delay Time		$t_{d(on)}$	–	42	–	ns	V_{GE} = 15V, V_{CC} = 400V, I_C = 60A, R_G = 7Ω, Inductive Load, T_{vj} = 25°C
Rise time		t_r	–	54	–		
Turn-off Delay Time		$t_{d(off)}$	–	142	–		
Fall Time		t_f	–	40	–		
Turn-on Switching Energy		E_{on}	–	0.92	–	mJ	
Turn-off Switching Energy		E_{off}	–	0.53	–		
Total Switching Energy		E_{ts}	–	1.45	–		
Reverse Recovery Time		t_{rr}	–	110	–	ns	I_F = 25A, di_F/dt = 500A/μs, T_{vj} = 25°C
Reverse Recovery Current		I_{rr}	–	18	–	A	
Reverse Recovery Charge		Q_{rr}	–	1.10	–	μC	
Turn-on Delay Time		$t_{d(on)}$	–	45	–	ns	V_{GE} = 15V, V_{CC} = 400V, I_C = 60A, R_G = 7Ω, Inductive Load, T_{vj} = 175°C
Rise time		t_r	–	58	–		
Turn-off Delay Time		$t_{d(off)}$	–	152	–		
Fall Time		t_f	–	35	–		
Turn-on Switching Energy		E_{on}	–	1.43	–	mJ	
Turn-off Switching Energy		E_{off}	–	0.53	–		
Total Switching Energy		E_{ts}	–	1.96	–		
Reverse Recovery Time		t_{rr}	–	205	–	ns	I_F = 25A, di_F/dt = 500A/μs, T_{vj} = 175°C
Reverse Recovery Current		I_{rr}	–	25	–	A	
Reverse Recovery Charge		Q_{rr}	–	2.67	–	μC	

Typical Performance Characteristics (@T_A = +25°C, unless otherwise specified.)

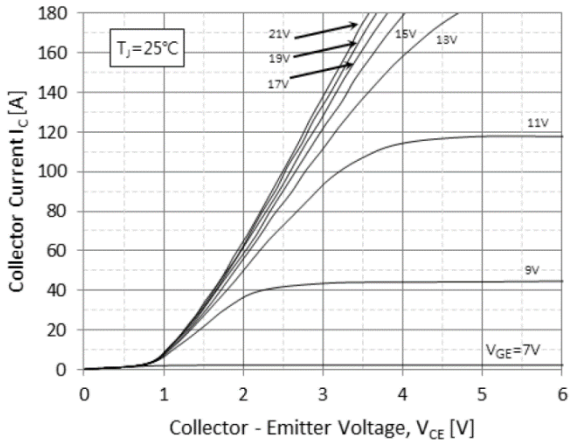


Fig.1 Typical Output Characteristics(T_J=25℃)

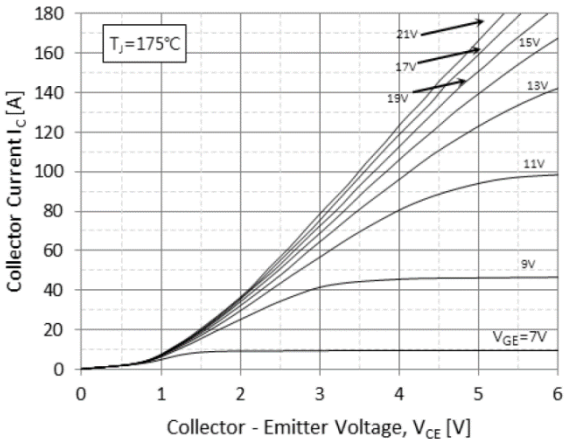


Fig.2 Typical Output Characteristics(T_J=175℃)

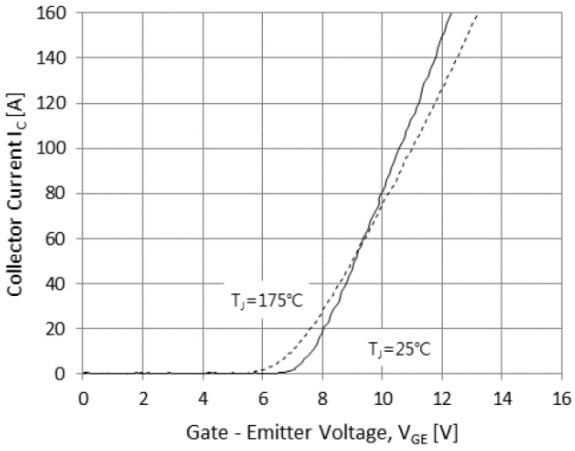


Fig.3 Typical Transfer Characteristics

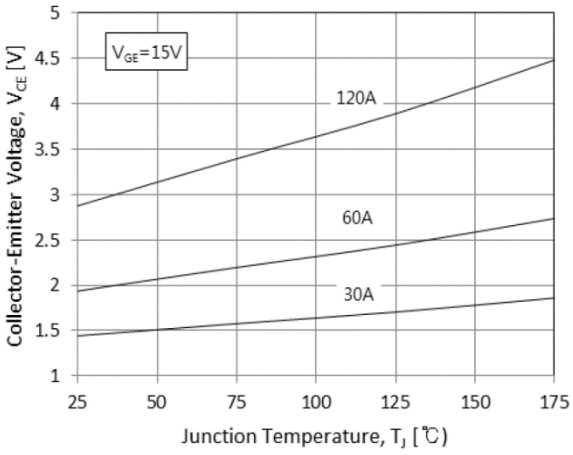


Fig.4 Typical Collector-Emitter Saturation Voltage -Junction Temperature

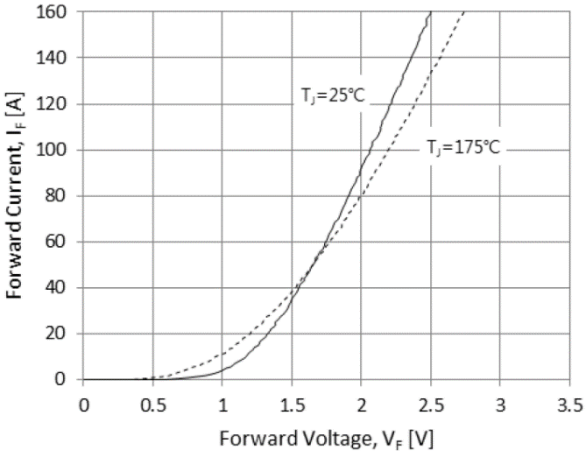


Fig.5 Diode Forward Characteristics

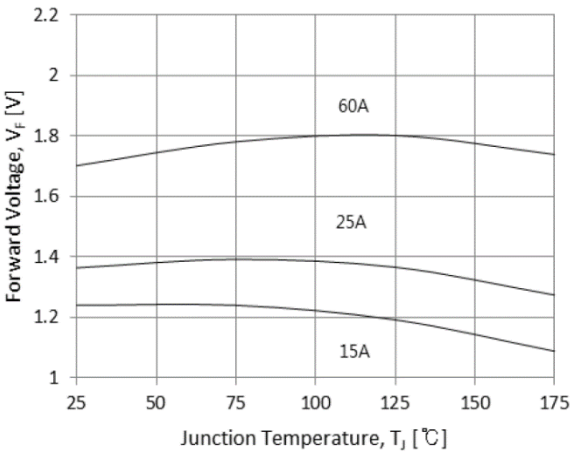


Fig.6 Diode Forward-Junction Temperature

Typical Performance Characteristics (continued)

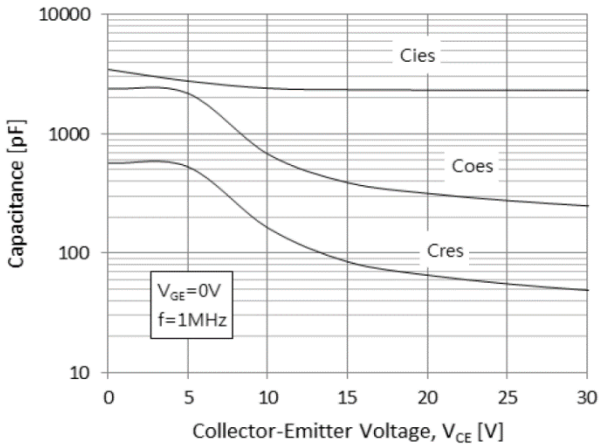


Fig.7 Typical Capacitance

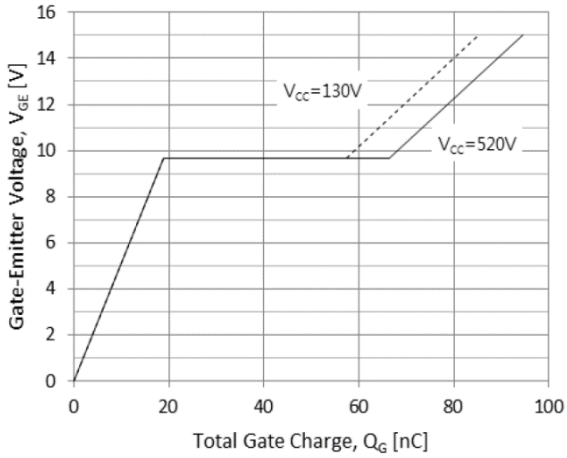


Fig.8 Typical Gate Charge

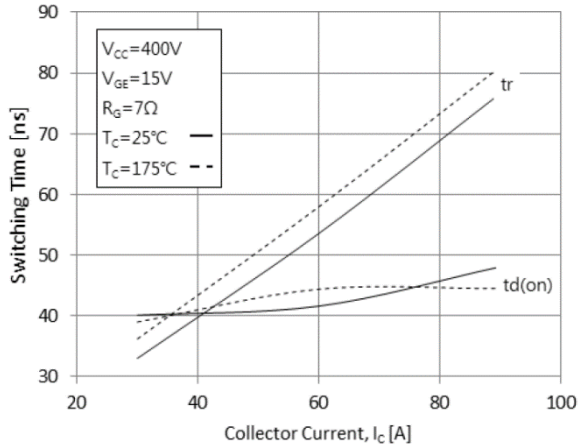


Fig.9 Typical Turn on-Collector Current

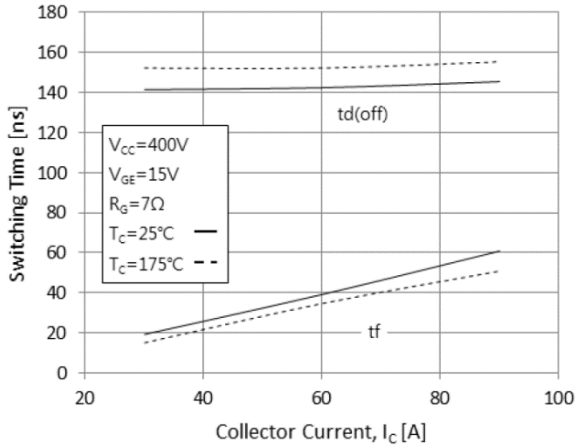


Fig.10 Typical Turn off-Collector Current

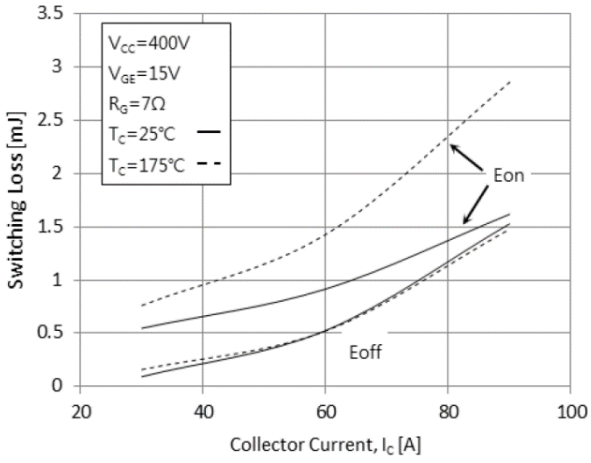


Fig.11 Switching Loss-Collector Current

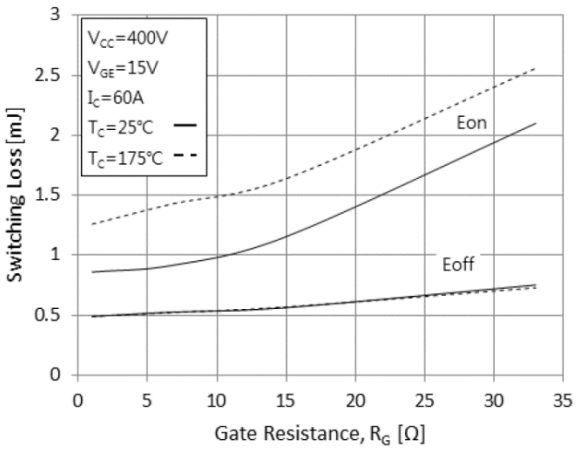


Fig.12 Switching Loss-Gate Resistance

Typical Performance Characteristics (cont.)

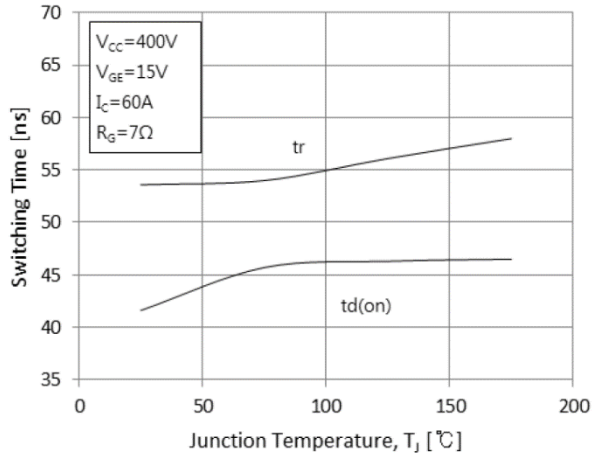


Fig.13 Turn on Characteristics-Junction Temperature

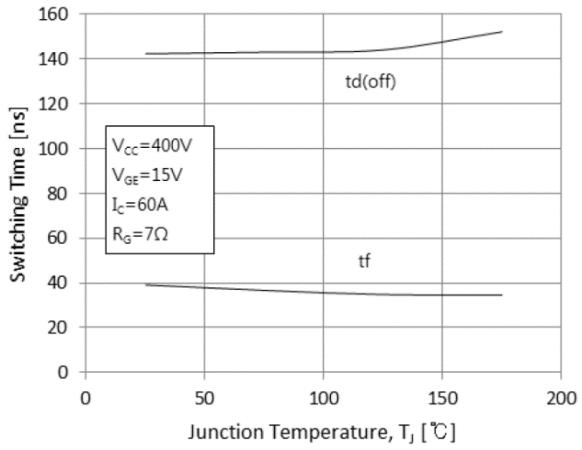


Fig.14 Turn off Characteristics-Junction Temperature

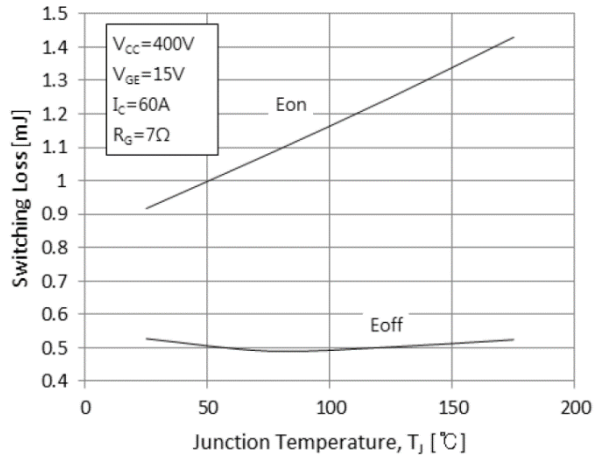


Fig.15 Switching Loss-Junction Temperature

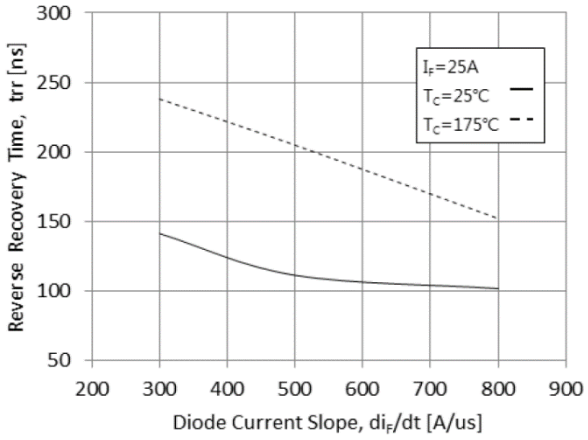


Fig.16 Reverse Recovery Time - Diode Current Slope

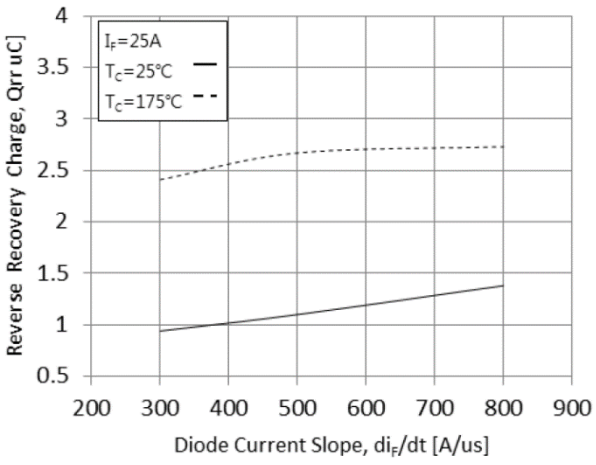


Fig.17 Reverse Recovery Charge - Diode Current Slope

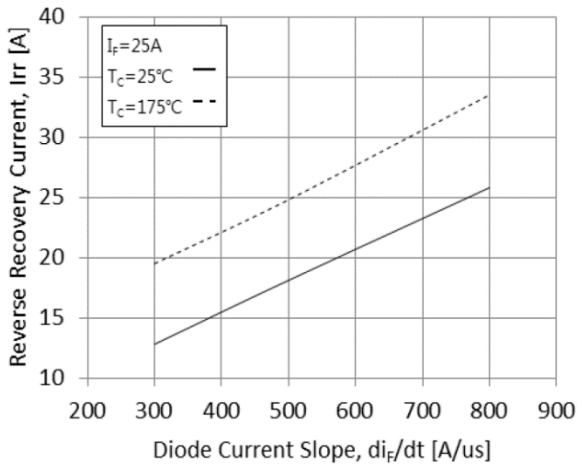


Fig.18 Reverse Recovery Current - Diode Current Slope

Typical Performance Characteristics (cont.)

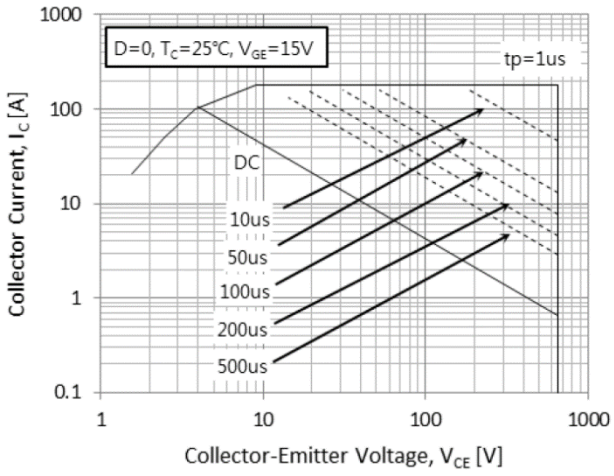


Fig.19 Forward Bias Safe Operating Area

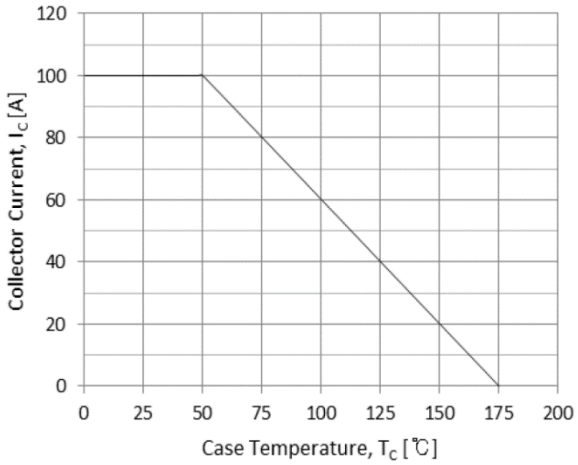


Fig.20 Case Temperature-Collector Current

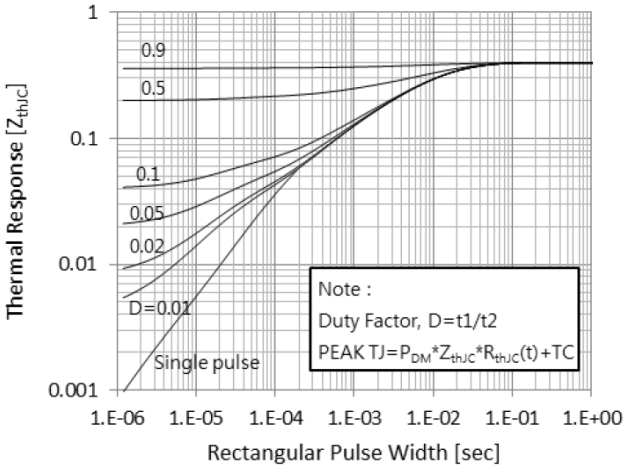


Fig.21 IGBT Transient Thermal Impedance

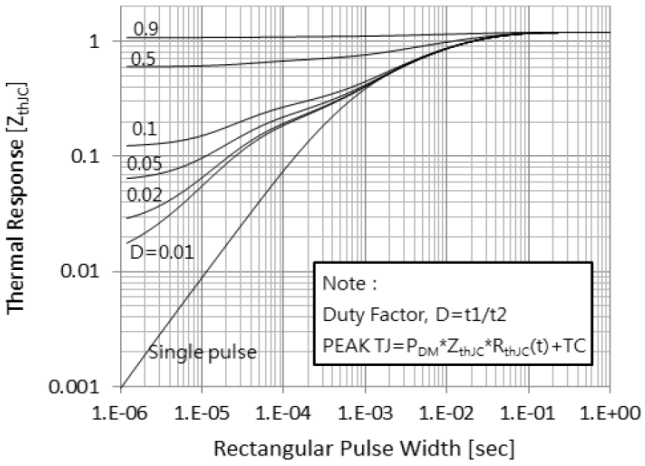
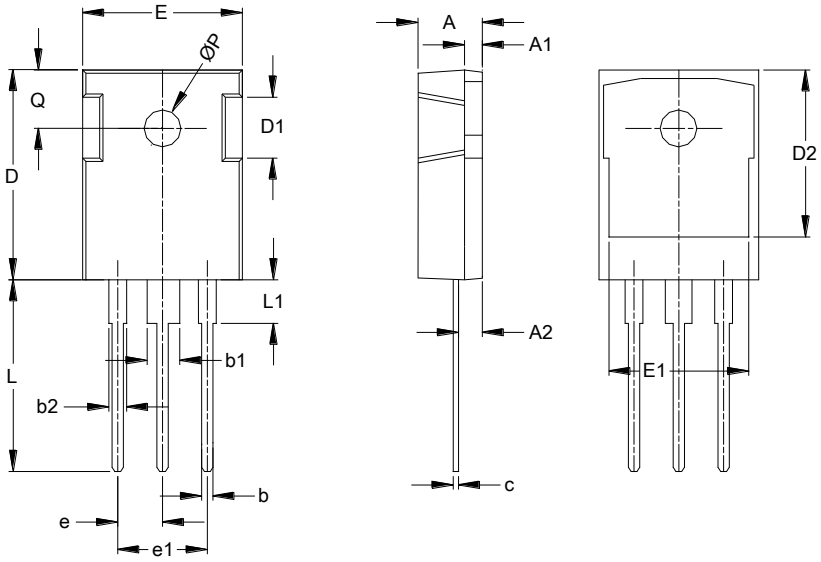


Fig.22 FRD Transient Thermal Impedance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO247 (Type MC)



TO-247 (Type MC)			
Dim	**Min**	**Max**	**Typ**
A	4.700	5.310	-
A1	1.500	2.490	-
A2	2.200	2.600	-
b	0.990	1.400	-
b1	2.590	3.430	-
b2	1.650	2.390	-
c	0.380	0.890	-
D	20.30	21.46	-
D1	4.320	5.490	-
D2	13.08	-	-
E	15.45	16.26	-
E1	13.06	14.02	-
e	5.450		
e1	10.90		
L	19.81	20.57	-
L1	-	4.500	-
Q	5.380	6.200	-
øP	3.500	3.700	-
All Dimensions in mm			

Note : For high-voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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